



Form PTO 1449 (Modified) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 246179US90DIV		SERIAL NO. 10/734,221	
		APPLICANT Hiroyuki NAGASAWA, et al.		FILING DATE December 15, 2003	
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*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.					